



The IBF-350 RE is designed for form error correction on nanometer scale and additionally for inert gas ion beam etching as well as for re-active ion beam etching. Backside cooling, work piece heating, SIMS for end point detection, interface for clean room, beam monitoring with Faraday cup array and other helpful features are available. This plant is able to perform sub-aperture re-active gas ion beam etching.

# IBF350RE

## TECHNICAL DATA

### WORK PIECE DATA

Diameter:	Ø350 mm (Ø14")
Thickness:	150 mm (6")
Weight:	max. 8.5 kg (16.5 lbs)
Contact angle:	0 – 90°
Rotation speed:	0 – 10 rpm
Shape:	plane, spherical, aspherical, freeform

### LOAD LOCK SYSTEM

Loading time:	< 2min.
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### AXIS SYSTEM

Type: 350RE	X, Y, Z, B, C
Travel:	X > 500 mm
	Y = 500 mm
	Z = 600mm
	B = 0 – 90°
	C = 360°, continuous

### ION BEAM SOURCES

Type K100 and type RF40

### DIMENSIONS

Weight:	5000 kg (11023 lbs)
WxHxD:	4.2 m x 2.4 m x 3.35 m (165" x 95" x 131")
Footprint:	6 m x 4 m (236" x 157")

